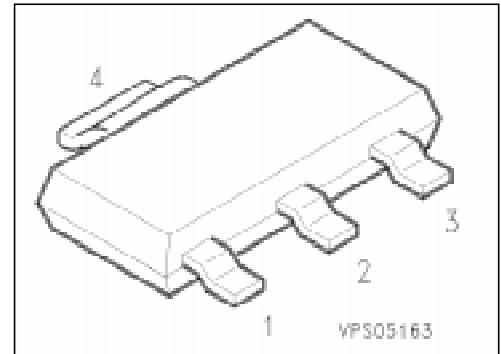


PNP Silicon Darlington Transistors

BCP 28
BCP 48

- For general AF applications
- High collector current
- High current gain
- Complementary types: BCP 29/49 (NPN)



Type	Marking	Ordering Code (tape and reel)	Pin Configuration	Package ¹⁾
BCP 28 BCP 48	BCP 28 BCP 48	Q62702-C2134 Q62702-C2135		SOT-223

Maximum Ratings

Parameter	Symbol	Values		Unit
		BCP 28	BCP 48	
Collector-emitter voltage	V_{CE0}	30	60	V
Collector-base voltage	V_{CB0}	40	80	
Emitter-base voltage	V_{EB0}	10	10	
Collector current	I_C	500		mA
Peak collector current	I_{CM}	800		
Base current	I_B	100		
Peak base current	I_{BM}	200		
Total power dissipation, $T_s = 124\text{ °C}^2)$	P_{tot}	1.5		W
Junction temperature	T_j	150		°C
Storage temperature range	T_{stg}	- 65 ... + 150		

Thermal Resistance

Junction - ambient ²⁾	$R_{th\ JA}$	≤ 75	K/W
Junction - soldering point	$R_{th\ JS}$	≤ 17	

¹⁾ For detailed information see chapter Package Outlines.

²⁾ Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm² Cu.

Electrical Characteristics

at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC characteristics

Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CE0}$				V
BCP 28		30	–	–	
BCP 48		60	–	–	
Collector-base breakdown voltage ¹⁾ $I_C = 100\text{ }\mu\text{A}, I_B = 0$	$V_{(BR)CB0}$				
BCP 28		40	–	–	
BCP 48		80	–	–	
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}, I_C = 0$	$V_{(BR)EB0}$	10	–	–	
Collector-base cutoff current $V_{CB} = 30\text{ V}, I_E = 0$	I_{CB0}				nA
BCP 28		–	–	100	
$V_{CB} = 60\text{ V}, I_E = 0$					nA
BCP 48		–	–	100	
$V_{CB} = 30\text{ V}, I_E = 0, T_A = 150\text{ }^\circ\text{C}$					μA
BCP 28		–	–	10	
$V_{CB} = 60\text{ V}, I_E = 0, T_A = 150\text{ }^\circ\text{C}$					μA
BCP 48		–	–	10	
Emitter-base cutoff current $V_{EB} = 4\text{ V}, I_C = 0$	I_{EB0}	–	–	100	nA
DC current gain ¹⁾ $I_C = 100\text{ }\mu\text{A}, V_{CE} = 1\text{ V}$	h_{FE}				–
BCP 28		4000	–	–	
BCP 48		2000	–	–	
$I_C = 10\text{ mA}, V_{CE} = 5\text{ V}$					
BCP 28		10000	–	–	
BCP 48		4000	–	–	
$I_C = 100\text{ mA}, V_{CE} = 5\text{ V}$					
BCP 28		20000	–	–	
BCP 48		10000	–	–	
$I_C = 500\text{ mA}, V_{CE} = 5\text{ V}$					
BCP 28		4000	–	–	
BCP 48		2000	–	–	
Collector-emitter saturation voltage $I_C = 100\text{ mA}, I_B = 0.1\text{ mA}$	V_{CEsat}	–	–	1.0	V
Base-emitter saturation voltage $I_C = 100\text{ mA}, I_B = 0.1\text{ mA}$	V_{BEsat}	–	–	1.5	

¹⁾ Pulse test conditions: $t \leq 300\text{ }\mu\text{s}, D \leq 2\%$.

Electrical Characteristics

at $T_A = 25\text{ °C}$, unless otherwise specified.

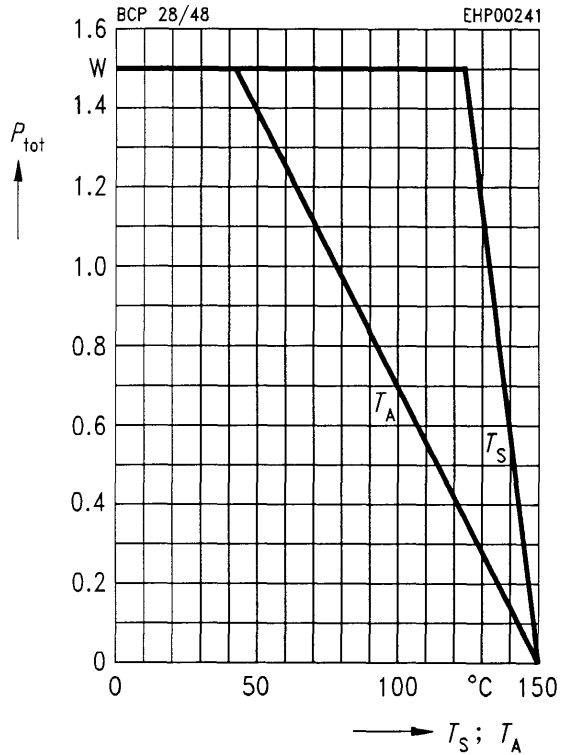
Parameter	Symbol	Values			Unit
		min.	typ.	max.	

AC characteristics

Transition frequency $I_C = 50\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 100\text{ MHz}$	f_t	–	200	–	MHz
Output capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{obo}	–	8	–	pF

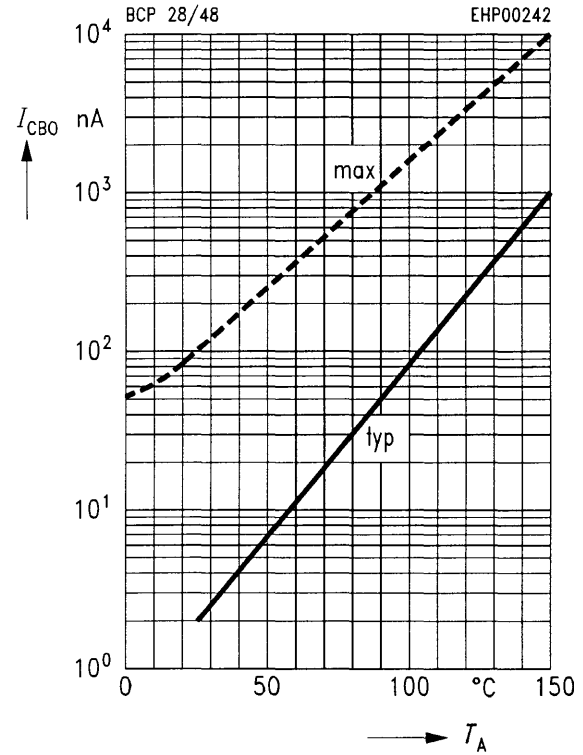
Total power dissipation $P_{tot} = f(T_A^*; T_S)$

* Package mounted on epoxy



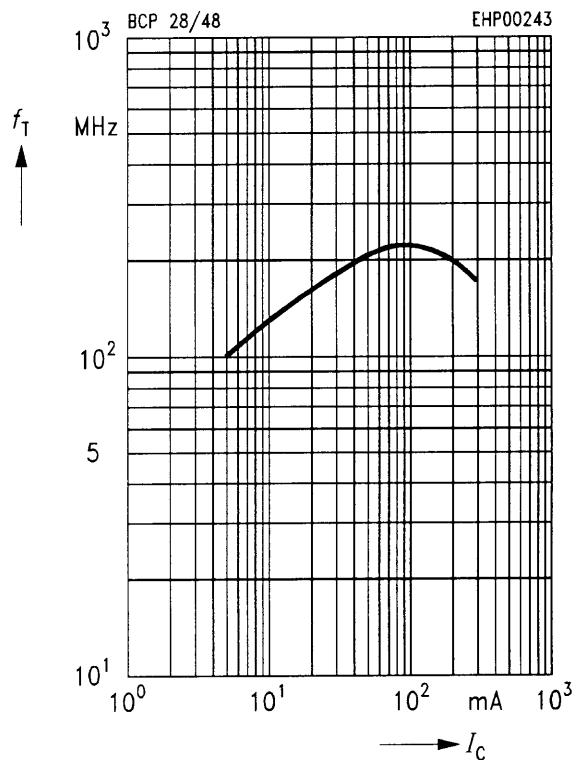
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CB} = V_{CE\ max}$

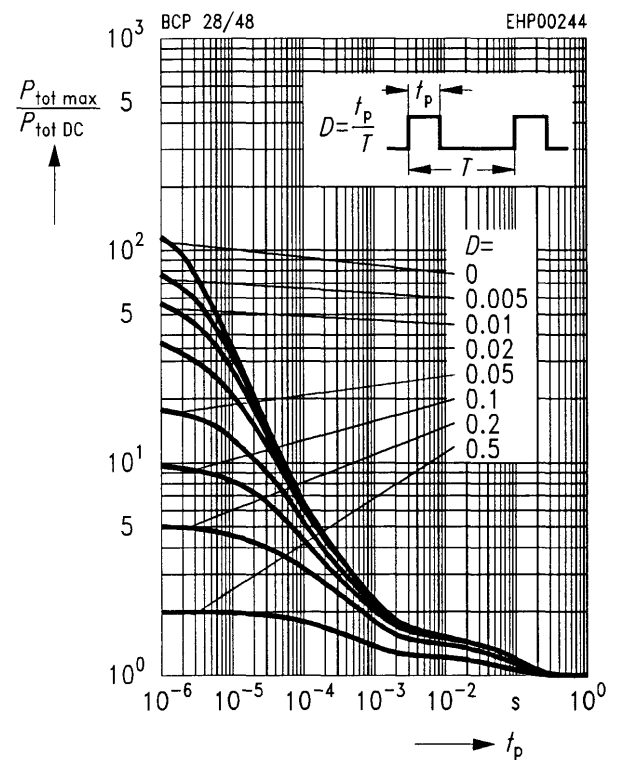


Transition frequency $f_T = f(I_C)$

$V_{CE} = 5\ V$

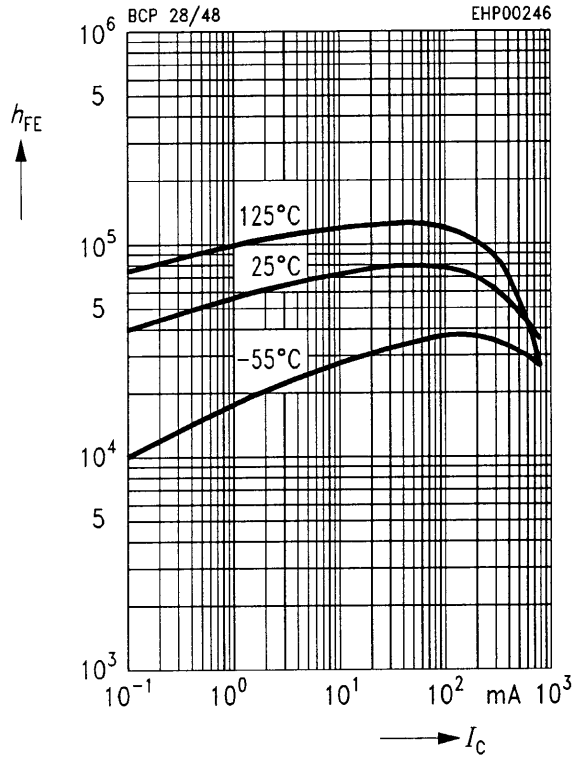


Permissible pulse load $P_{tot\ max}/P_{tot\ DC} = f(t_p)$



DC current gain $h_{FE} = f(I_C)$

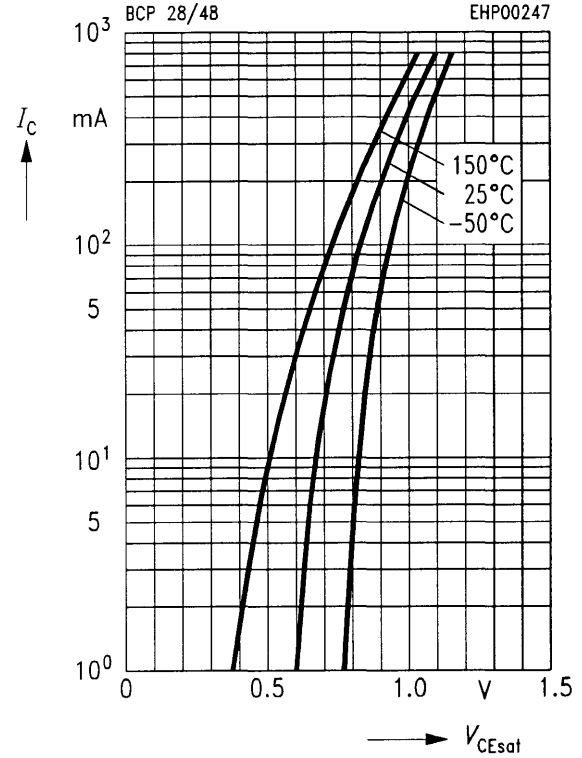
$V_{CE} = 5\text{ V}$



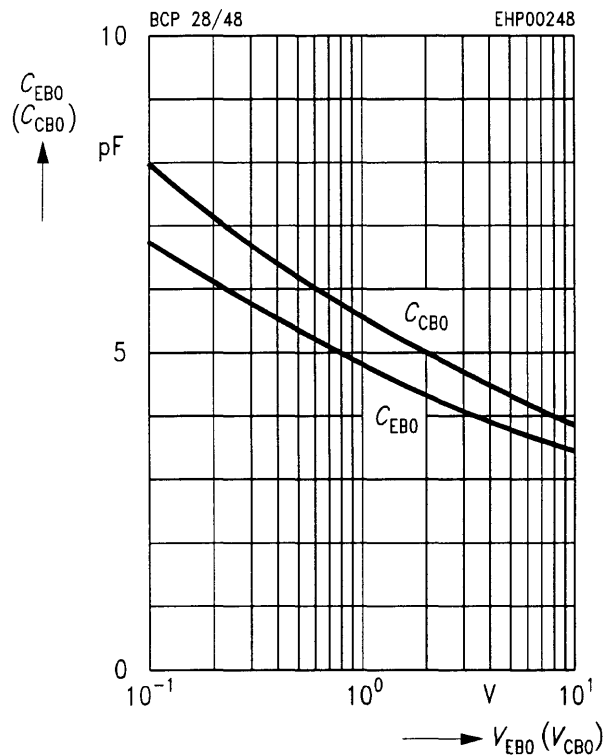
Collector-emitter saturation voltage

$I_C = f(V_{CEsat})$

$h_{FE} = 1000$



Collector-base capacitance $C_{CB0} = f(V_{CB0})$
Emitter-base capacitance $C_{EB0} = f(V_{EB0})$



Base-emitter saturation voltage

$I_C = f(V_{BEsat})$

$h_{FE} = 1000$

